



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

<p>In re application of: Harry S. Luan, et al. Serial No.: 10/777,560 Filed: February 11, 2004 For: STACKABLE RESISTIVE CROSS-POINT MEMORY WITH SCHOTTKY DIODE ISOLATION</p>	<p>Examiner: Thinh Nguyen Art Unit: 2818</p> <p style="text-align: center;">INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR §1.97 and §1.98</p>
--	---

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

The references cited on attached form PTO-1449 are being called to the attention of the Examiner. Copies of the references are enclosed. It is respectfully requested that the cited information be expressly considered during the prosecution of this application, and the references be made of record therein and appear among the "references cited" on any patent to issue there from.

As provided for by 37 CFR 1.97(g) and (h), no inference should be made that the information and references cited are prior art merely because they are in this statement and no representation is being made that a search has been conducted or that this statement encompasses all the possible relevant information.

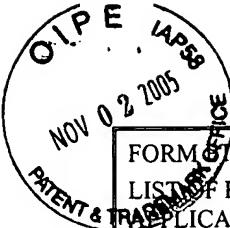
The Commissioner is authorized to deduct such fee from the undersigned's Deposit Account No. 50-1229. Please deduct any additional fees from, or credit any overpayment to, the above-noted Deposit Account.

Respectfully submitted,

Truong T. Dinh
Reg. No. 40,993

11/03/2005 DEMMANU1 00000006 501229 10777560
01 FC:1806 180.00 DA

<p>DINH & ASSOCIATES 2506 Ash Street Palo Alto, California 94306 Tel: (650) 289-0600 Fax: (650) 289-0700</p>	<p>I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450</p> <p>By: On: <u>October 26, 2005</u></p>
--	---



FORM GTO-1449 (Modified)		Attorney Docket No.: 108-18.1		Application No.: 10/777,560	
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Applicant: Harry S. Luan, et al.			
		Filing Date: February 11, 2004		Group:	
Reference Designation		U.S. PATENT DOCUMENTS			
Examiner Initial	Document No.	Date	Name	Class	Sub-class
AA	6,204,139	3/20/01	Liu et al	438	385
AB	6,531,371	3/11/03	Hsu et al	438	385
AC					
AD					
AE					
AF					
AG					
AH					
AI					
AJ					
AK					
AL					
AM					
AN					
AO					
FOREIGN PATENT DOCUMENTS					
	Document No.	Date	Country	Class	Sub-class
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)					
AP	Zhuang et al., "Novell Colossal Magnetoresistive Thin Film Nonvolatile Resistance Random Access Memory (RRAM)," IEEE 2002.				
AQ	Liu et al., "A New Concept for Non-Volatile Memory: The Electric Pulse Induced Resistive Change Effect in Colossal Magnetoresistive Thin Films,"				
AR	Liu et al., "Electric-pulse-induced reversible resistance change effect in magnetoresistive films," American Institute of Physics, 2000, pg. 2749-2751.				
AS					
AT					
AU					
AV					
AW					
AX					
EXAMINER	DATE CONSIDERED				

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.